## *Opti*MOS®3 Power-Transistor

Features

• Fast switching MOSFET for SMPS

• Optimized technology for DC/DC converters

• Qualified according to JEDEC[1] for target applications

• N-channel, logic level

• Excellent gate charge x $R_{DS(on)}$ product (FOM)

• Very low on-resistance $R_{DS(on)}$

• Avalanche rated

• Pb-free plating; RoHS compliant

Product Summary

V_{DS}	30	V
$R_{DS(on),max}$	9	mΩ
I_D	40	A

drain pin 2
gate pin 1
source pin 3
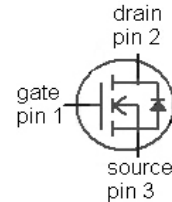
Type	IPD090N03L G	IPF090N03L G	IPS090N03L G	IPU090N03L G
Package	PG-TO252-3-11	PG-TO252-3-23	PG-TO251-3-11	PG-TO251-3-21
Marking	090N03L	090N03L	090N03L	090N03L

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	V_{GS}=10 V, T_C=25 °C	40	A
		V_{GS}=10 V, T_C=100 °C	37	
		V_{GS}=4.5 V, T_C=25 °C	40	
		V_{GS}=4.5 V, T_C=100 °C	30	
Pulsed drain current[2]	$I_{D,pulse}$	T_C=25 °C	280	
Avalanche current, single pulse[3]	I_{AS}	T_C=25 °C	40	
Avalanche energy, single pulse	E_{AS}	I_D=12 A, R_{GS}=25 Ω	40	mJ
Reverse diode dv/dt	dv/dt	I_D=40 A, V_{DS}=24 V, di/dt=200 A/μs, $T_{j,max}$=175 °C	6	kV/μs
Gate source voltage	V_{GS}		±20	V

[1] J-STD20 and JESD22

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Power dissipation	P_{tot}	T_C=25 °C	42	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	-	3.6	K/W
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	75	
		6 cm² cooling area[4]	-	-	50	

Electrical characteristics, at T_j=25 °C, unless otherwise specified

Static characteristics

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=1 mA	30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250 µA	1	-	2.2	
Zero gate voltage drain current	I_{DSS}	V_{DS}=30 V, V_{GS}=0 V, T_j=25 °C	-	0.1	1	µA
		V_{DS}=30 V, V_{GS}=0 V, T_j=125 °C	-	10	100	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=0 V	-	10	100	nA
Drain-source on-state resistance[5]	$R_{DS(on)}$	V_{GS}=4.5 V, I_D=30 A	-	10.8	13.5	mΩ
		V_{GS}=10 V, I_D=30 A	-	7.5	9	
Gate resistance	R_G		-	1.1	-	Ω
Transconductance	g_{fs}	$|V_{DS}|$>2$|I_D|R_{DS(on)max}$, I_D=30 A	28	55	-	S

[2] See figure 3 for more detailed information

[3] See figure 13 for more detailed information

[4] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

[5] Measured from drain tab to source pin

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=15 V, f=1 MHz	-	1200	1600	pF
Output capacitance	C_{oss}		-	500	660	
Reverse transfer capacitance	C_{rss}		-	24	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=15 V, V_{GS}=10 V, I_D=30 A, R_G=1.6 Ω	-	4	-	ns
Rise time	t_r		-	14	-	
Turn-off delay time	$t_{d(off)}$		-	15	-	
Fall time	t_f		-	3	-	

Gate Charge Characteristics[6]

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Gate to source charge	Q_{gs}	V_{DD}=15 V, I_D=30 A, V_{GS}=0 to 4.5 V	-	4.0	-	nC
Gate charge at threshold	$Q_{g(th)}$		-	1.9	-	
Gate to drain charge	Q_{gd}		-	1.8	-	
Switching charge	Q_{sw}		-	3.9	-	
Gate charge total	Q_g		-	7.4	-	
Gate plateau voltage	$V_{plateau}$		-	3.4	-	V
Gate charge total	Q_g	V_{DD}=15 V, I_D=30 A, V_{GS}=0 to 10 V	-	15	-	
Gate charge total, sync. FET	$Q_{g(sync)}$	V_{DS}=0.1 V, V_{GS}=0 to 4.5 V	-	6.4	-	nC
Output charge	Q_{oss}	V_{DD}=15 V, V_{GS}=0 V	-	13	-	

Reverse Diode

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Diode continuous forward current	I_S	T_C=25 °C	-	-	37	A
Diode pulse current	$I_{S,pulse}$		-	-	280	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=30 A, T_j=25 °C	-	0.91	1.1	V
Reverse recovery charge	Q_{rr}	V_R=15 V, I_F=I_S, di_F/dt=400 A/µs	-		10	nC

[6] See figure 16 for gate charge parameter definition

1 Power dissipation

P_{tot}=f(T_C)
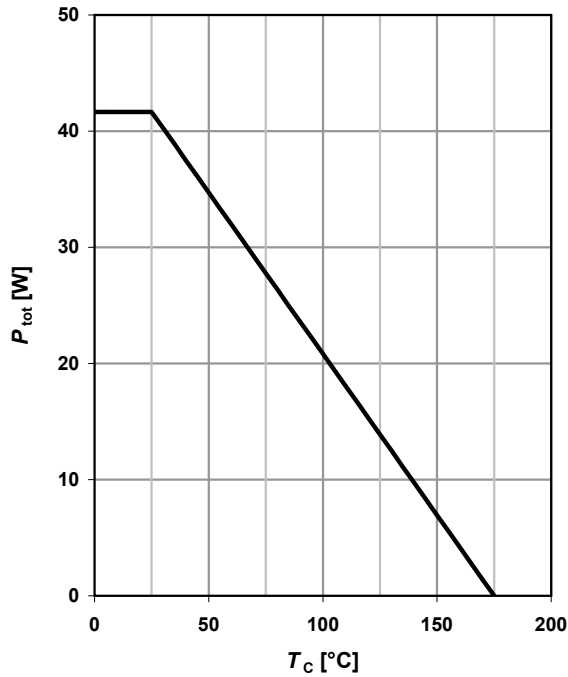
2 Drain current

I_D=f(T_C); V_{GS}≥10 V
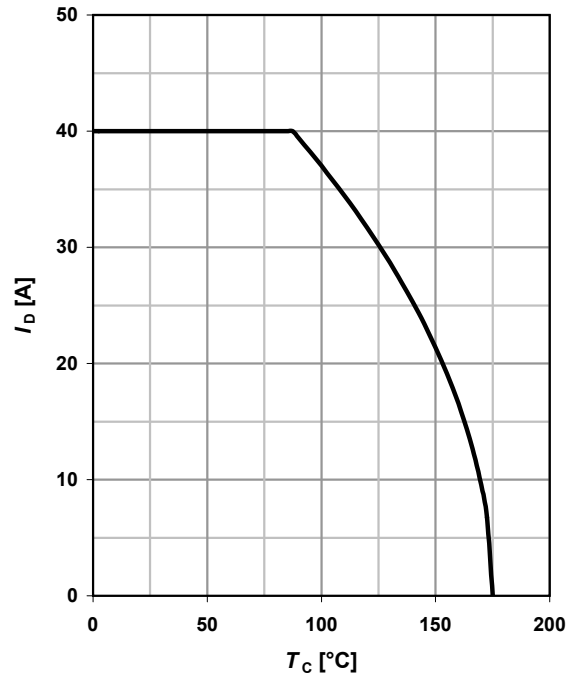
3 Safe operating area

I_D=f(V_{DS}); T_C=25 °C; D=0
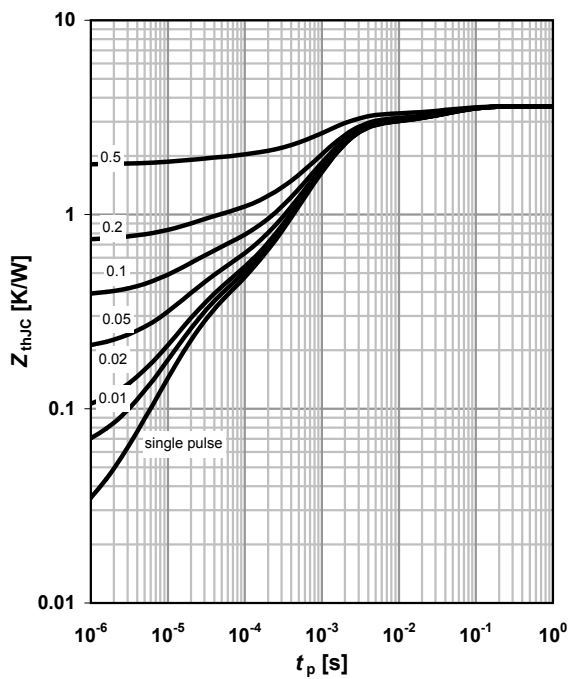
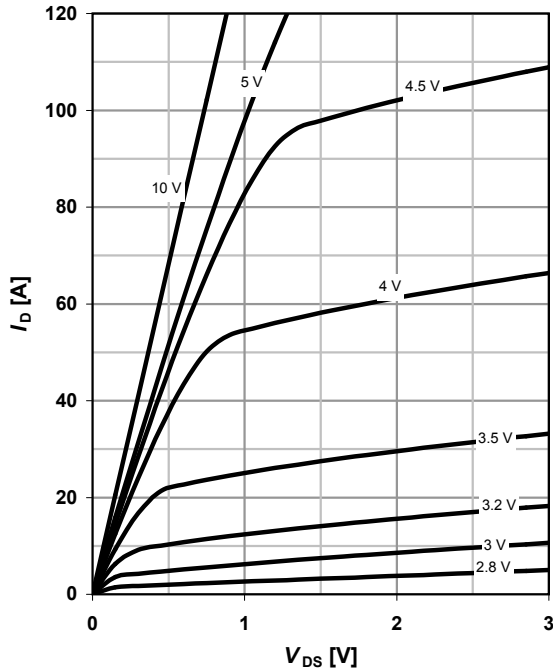parameter: t_p
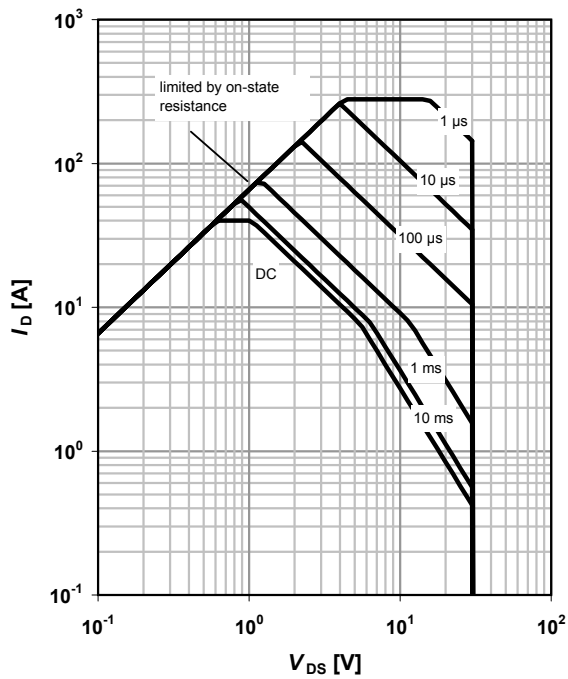
4 Max. transient thermal impedance

Z_{thJC}=f(t_p)

parameter: D=t_p/T
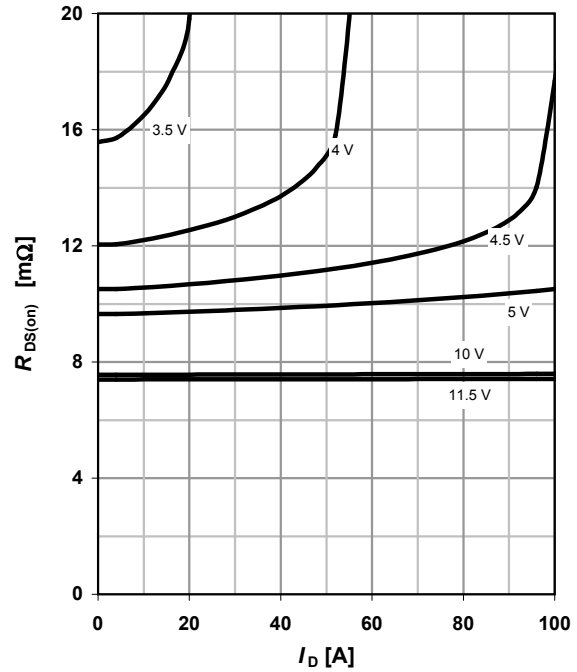
5 Typ. output characteristics

I_D=f(V_{DS}); T_j=25 °C

parameter: V_{GS}

6 Typ. drain-source on resistance

$R_{DS(on)}$=f(I_D); T_j=25 °C

parameter: V_{GS}

7 Typ. transfer characteristics

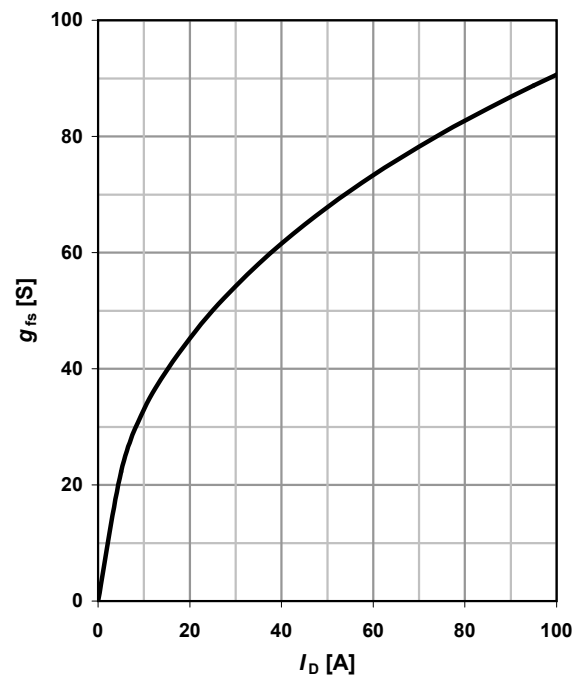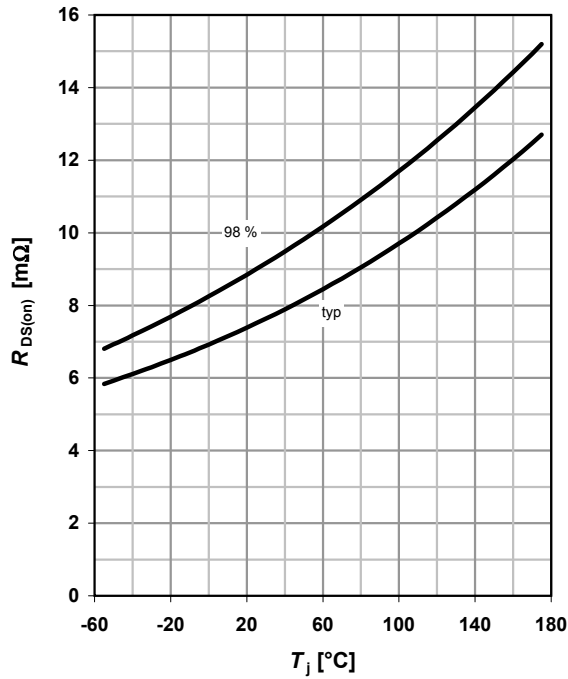I_D=f(V_{GS}); $|V_{DS}|$>2$|I_D|R_{DS(on)max}$

parameter: T_j
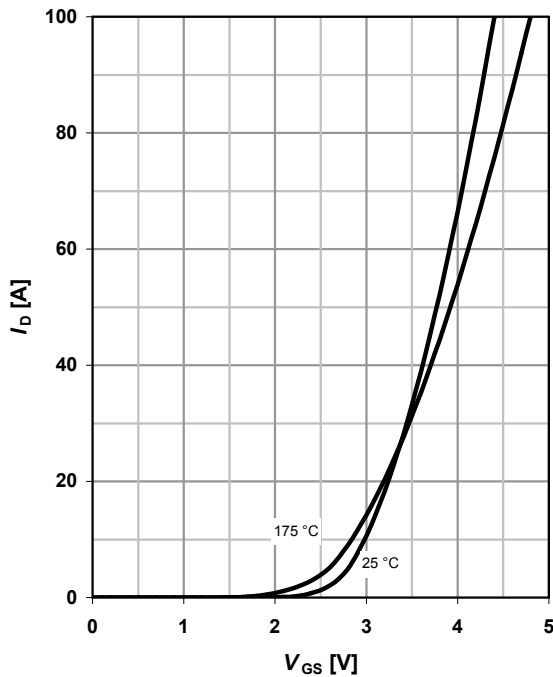
8 Typ. forward transconductance

g_{fs}=f(I_D); T_j=25 °C

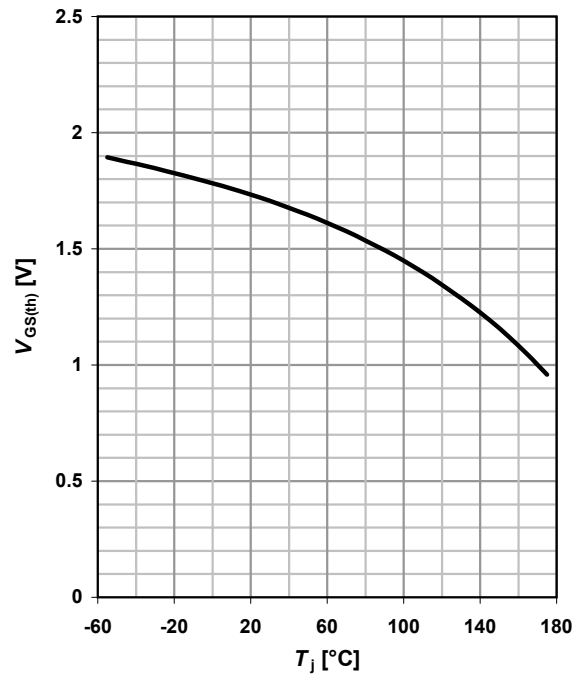## 9 Drain-source on-state resistance

$R_{DS(on)}$=f(T_j); I_D=30 A; V_{GS}=10 V

10 Typ. gate threshold voltage

$V_{GS(th)}$=f(T_j); V_{GS}=V_{DS}; I_D=250 µA

11 Typ. capacitances

C=f(V_{DS}); V_{GS}=0 V; f=1 MHz
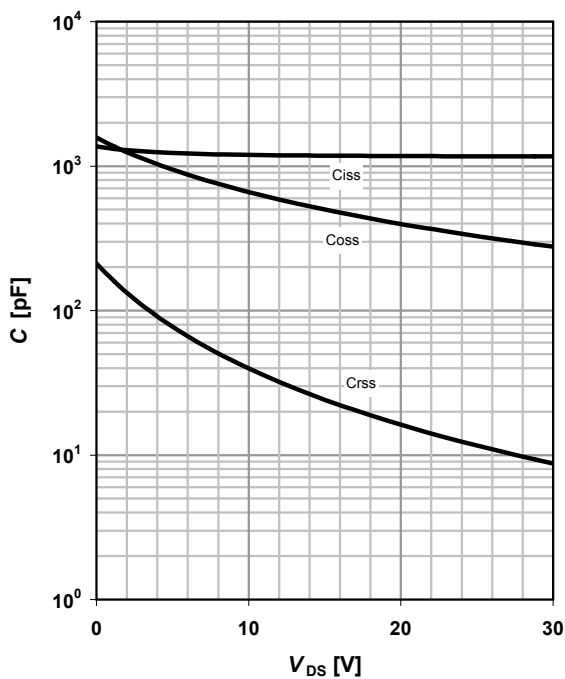
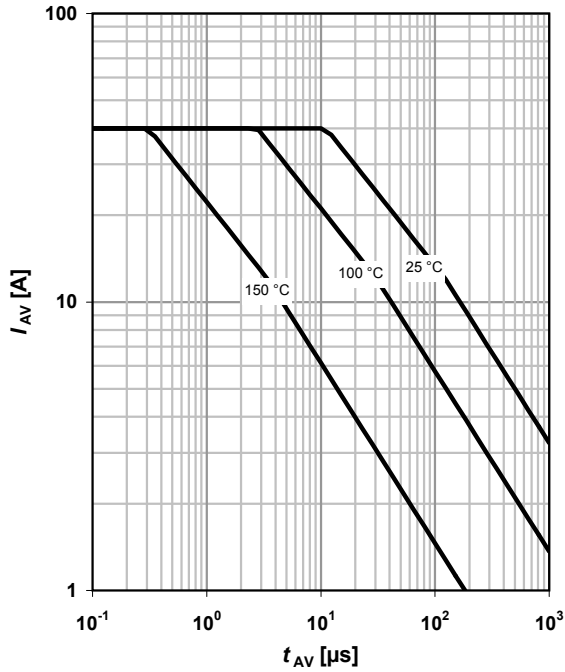## 12 Forward characteristics of reverse diode

I_F=f(V_{SD})

parameter: T_j
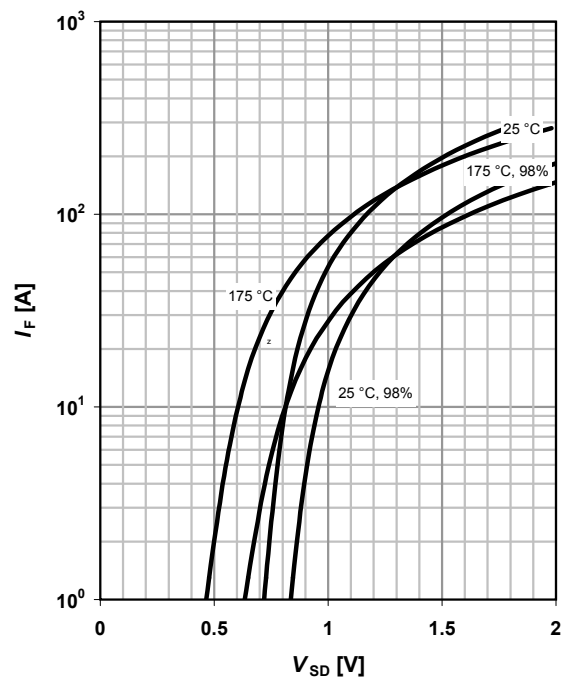
13 Avalanche characteristics

I_{AS}=f(t_{AV}); R_{GS}=25 Ω
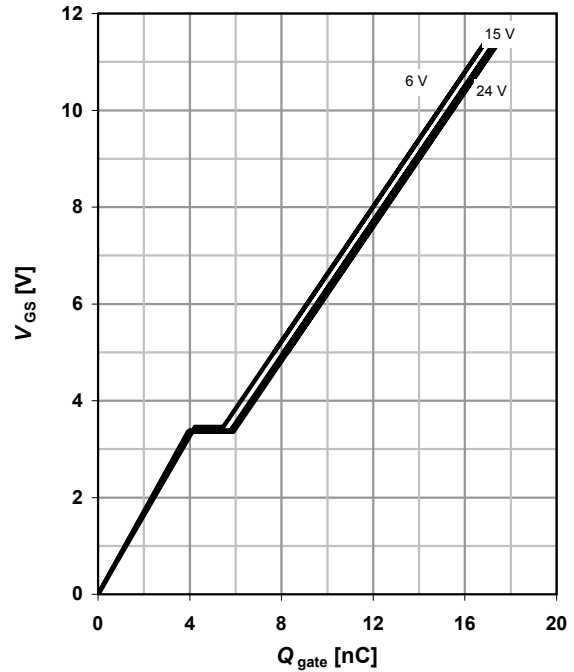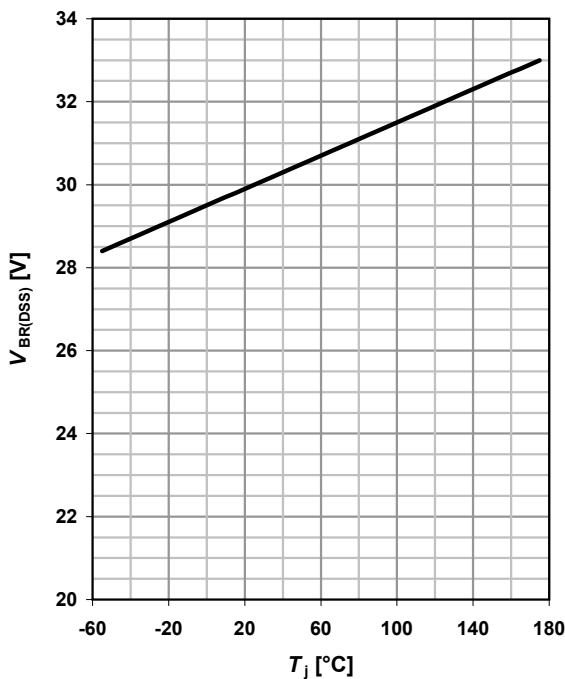
parameter: $T_{j(start)}$

14 Typ. gate charge

V_{GS}=f(Q_{gate}); I_D=30 A pulsed

parameter: V_{DD}

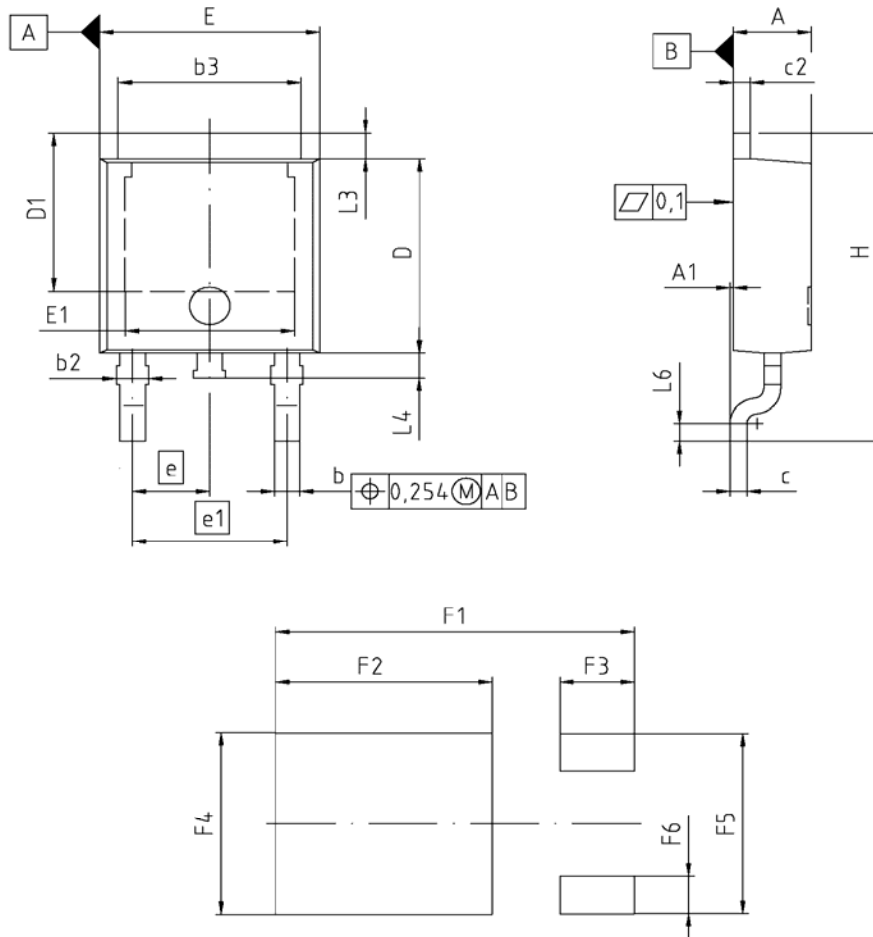### 15 Drain-source breakdown voltage

$V_{BR(DSS)}$=f(T_j); I_D=1 mA

16 Gate charge waveforms

Package Outline **PG-TO252-3-11**

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.159	2.413	0.085	0.095
A1	0.000	0.150	0.000	0.006
b	0.635	0.889	0.025	0.035
b2	0.650	1.150	0.026	0.045
b3	5.004	5.500	0.197	0.217
c	0.457	0.580	0.018	0.023
c2	0.460	0.980	0.018	0.039
D	5.969	6.223	0.235	0.245
D1	5.020	5.842	0.198	0.230
E	6.400	6.731	0.252	0.265
E1	4.850	5.207	0.191	0.205
e	2.286		0.090	
e1	4.572		0.180	
N	3		3	
H	9.400	10.480	0.370	0.413
L3	0.900	1.143	0.035	0.045
L4	0.584	0.950	0.023	0.037
L6	0.510	0.686	0.020	0.027
F1	10.500	10.700	0.413	0.421
F2	6.300	6.500	0.248	0.256
F3	2.100	2.300	0.083	0.091
F4	5.700	5.900	0.224	0.232
F5	5.660	5.860	0.222	0.231
F6	1.100	1.300	0.043	0.051

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JEDEC TO252

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Package Outline   **PG-TO252-3-23**

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.159	2.413	0.085	0.095
A1	0.000	0.150	0.000	0.006
b	0.635	0.889	0.025	0.035
b2	0.650	1.150	0.026	0.045
b3	5.004	5.500	0.197	0.217
c	0.457	0.580	0.018	0.023
c2	0.460	0.980	0.018	0.039
D	5.969	6.223	0.235	0.245
D1	5.020	5.842	0.198	0.230
E	6.400	6.731	0.252	0.265
E1	4.850	5.207	0.191	0.205
e	2.286		0.090	
e1	4.572		0.180	
N	3		3	
H	9.400	10.480	0.370	0.413
L3	0.900	1.143	0.035	0.045
L4	0.584	0.950	0.023	0.037
L6	0.510	0.696	0.020	0.027
F1	10.500	10.700	0.413	0.421
F2	6.300	6.500	0.248	0.256
F3	2.100	2.300	0.083	0.091
F4	5.700	5.900	0.224	0.232
F5	5.660	5.860	0.222	0.231
F6	1.100	1.300	0.043	0.051

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Package Outline   **PG-TO251-3-11**
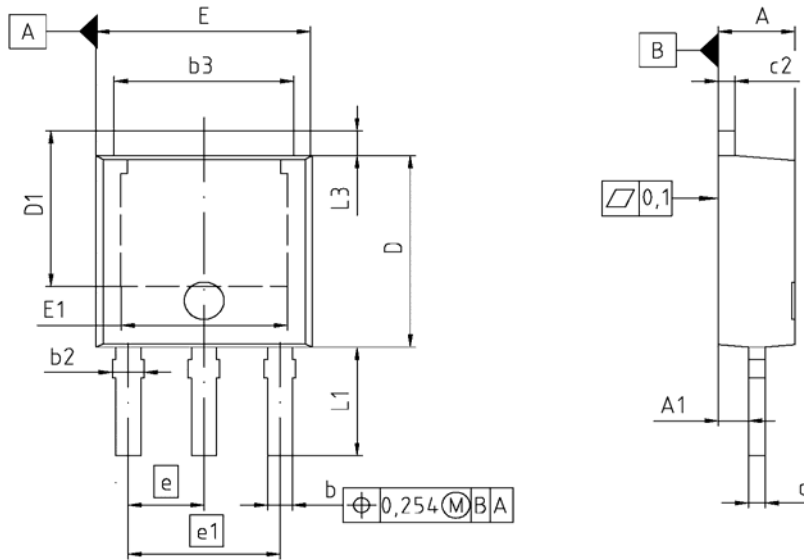
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.184	2.388	0.086	0.094
A1	0.000	0.150	0.000	0.006
b	0.635	0.889	0.025	0.035
b2	0.650	1.150	0.025	0.045
b3	5.004	5.500	0.197	0.217
c	0.460	0.580	0.018	0.023
c2	0.460	0.980	0.018	0.039
D	5.969	6.223	0.235	0.245
D1	5.020	5.320	0.198	0.209
E	6.400	6.731	0.252	0.265
E1	4.900	5.100	0.193	0.201
e	2.286		0.090	
e1	4.572		0.180	
N	3		3	
L1	3.400	3.600	0.134	0.142
L3	0.900	1.118	0.035	0.044

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Package Outline   **PG-TO251-3-21**
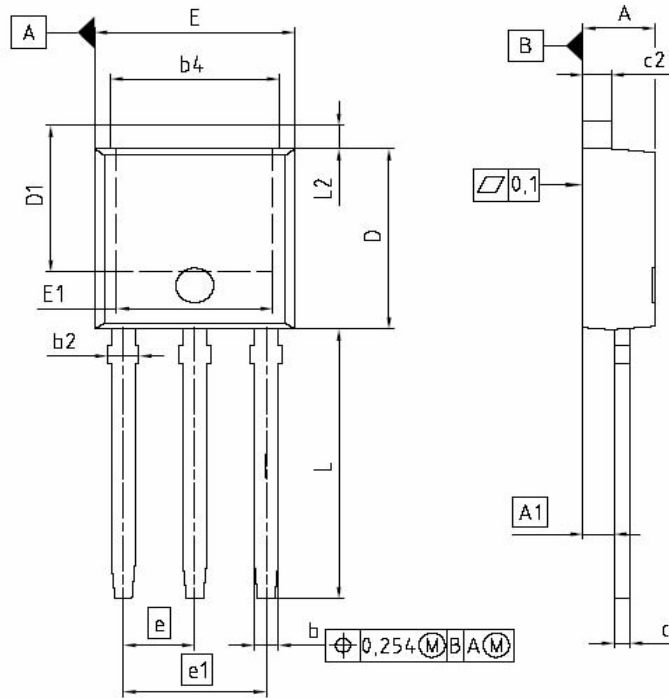
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.159	2.413	0.085	0.095
A1	0.900	1.118	0.035	0.044
b	0.650	0.850	0.026	0.033
b2	0.650	1.150	0.026	0.045
b4	5.004	5.500	0.197	0.217
c	0.457	0.580	0.018	0.023
c2	0.737	0.980	0.029	0.039
D	5.969	6.223	0.235	0.245
D1	5.100	6.121	0.201	0.241
E	6.400	6.731	0.252	0.265
E1	4.850	5.207	0.191	0.205
e	2.286		0.090	
e1	4.572		0.180	
N	3		3	
L	8.900	9.525	0.350	0.375
L1	0.900	1.143	0.035	0.045

REFERENCE
JEDEC TO251

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01-08-2005

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TO251_1

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